

Amendment to the Specification

Please amend paragraph [0031] as follows, wherein deletions are shown in strikeout:

Preferably that the metal hard-mask film 120 is formed by use of materials which are the same as a metal film constituting the bit line, so as to easily remove the metal hard-mask film 120 from the second interlayer insulation film 118 in a subsequent planarization process using chemical and mechanical processes after burying metal in a bit line trench. Preferably the metal hard-mask film 120 is formed by use of materials having etching selectivity larger than that of the second interlayer insulation film 118. Therefore, it is possible to prevent critical dimensions of the bit line from being broader in the following etching process of forming the bit line trench and cleaning process. In this embodiment, it is preferable that the metal hard- mask film 120 is formed using tungsten (W) film. The thickness of the tungsten film should be sufficient to endure as an etching barrier in the following process of etching the oxide film. Preferably the tungsten film has a thickness of about 500 Å to 1000 Å.